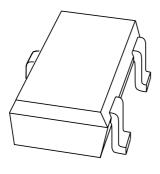
DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS4140U 40 V low V_{CEsat} NPN transistor

Product data sheet Supersedes data of 2001 Mar 27 2001 Jul 13



40 V low V_{CEsat} NPN transistor

PBSS4140U

FEATURES

- · Low collector-emitter saturation voltage
- · High current capabilities.
- Improved device reliability due to reduced heat generation.
- Enhanced performance over SOT231A general purpose packaged transistors.

APPLICATIONS

- · General purpose switching and muting
- · LCD backlighting
- · Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT323 plastic package. PNP complement: PBSS5140U.

MARKING

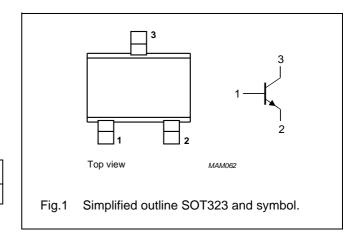
TYPE NUMBER	MARKING CODE
PBSS4140U	41t

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	40	V
I _{CM}	peak collector current	2	Α
R _{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V _{CEO}	collector-emitter voltage	open base	_	40	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	1	Α
I _{CM}	peak collector current		_	2	А
I _{BM}	peak base current		_	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
		T _{amb} ≤ 25 °C; note 2	_	350	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.
- 2. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air; note 1	500	K/W
	ambient	in free air; note 2	357	K/W

Notes

- 1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
- 2. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm².

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

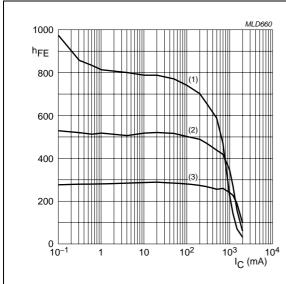
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off	V _{CB} = 40 V; I _C = 0	_	_	100	nA
	current	V _{CB} = 40 V; I _C = 0; T _{amb} = 150 °C	_	-	50	μΑ
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_B = 0$	_	_	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	300	_	_	
		V _{CE} = 5 V; I _C = 500 mA	300	-	900	
		V _{CE} = 5 V; I _C = 1 A	200	_	-	
V _{CEsat}	collector-emitter saturation	I _C = 100 mA; I _B = 1 mA	_	_	200	mV
	voltage	I _C = 500 mA; I _B = 50 mA	_	_	250	mV
		I _C = 1 A; I _B = 100 mA	_	_	500	mV
R _{CEsat}	equivalent on-resistance	$I_C = 500 \text{ mA}$; $I_B = 50 \text{ mA}$; note 1	_	260	<500	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA	_	_	1.2	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 5 V; I _C = 1 A	_	_	1.1	V
f _T	transition frequency	$I_C = 50 \text{ mA}; V_{CE} = 10 \text{ V}; f = 100 \text{ MHz}$	150	_	_	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	_	10	pF

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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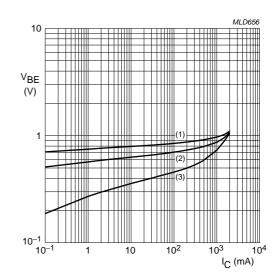
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 $V_{CE} = 5 V$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

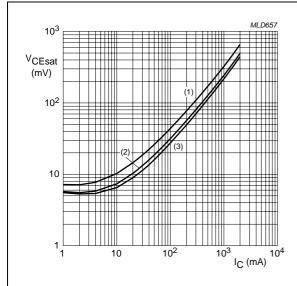
Fig.2 DC current gain as a function of collector current; typical values.



V_{CE} = 5 V.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

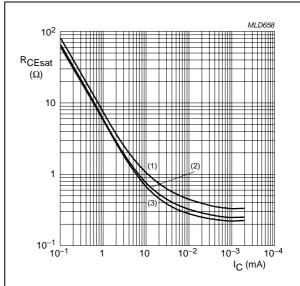
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.5 Equivalent on-resistance as a function of collector current; typical values.

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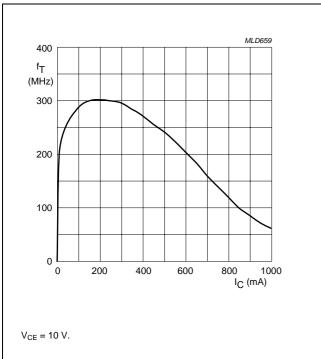


Fig.6 Transition frequency as a function of collector current; typical values.

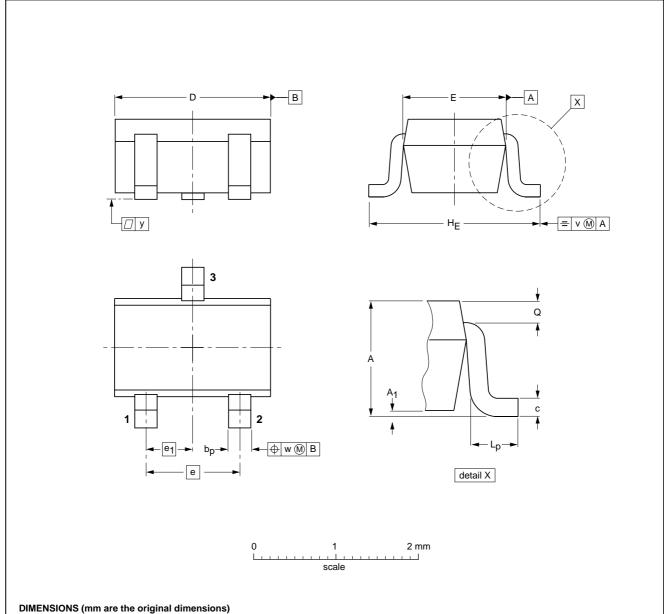
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (r	mm are the	original o	dimensions)
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Į.	UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
	mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT323			SC-70		$ \ \ \bigoplus \big($	97-02-28

2001 Jul 13 6

40 V low V_{CEsat} NPN transistor

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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